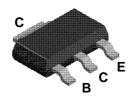


July 1998

NZT660 / NZT660A



SOT-223

PNP Low Saturation Transistor

v saturation vc' These devices are designed with high current gain and low saturation voltage with collector currents up to 3A continuous.

Absolute Maximum Ratings*

Symbol	Parameter	NZT660/NZT660A	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	3	Α
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

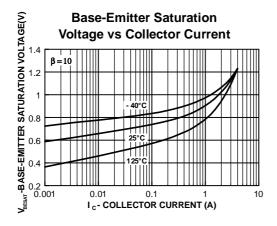
- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

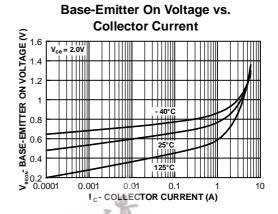
Thermal Characteristics T_{A = 25°C} unless otherwise noted

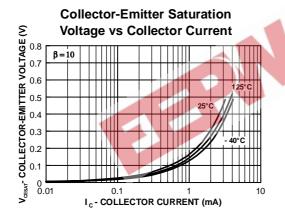
Symbol	Characteristic	Мах	Units
		NZT660/NZT660A	
P _D	Total Device Dissipation	2	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	°C/W

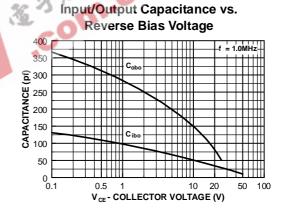
Symbol	Parameter	Test Conditions	Min	Max	Units
OEE CUA	RACTERISTICS			1	ı
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA	60		V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 100 \mu\text{A}$	80		V
BV _{EBO}	Emitter-Base Breakdown Voltage	Ι _Ε = 100 μΑ	5		V
Ісво	Collector Cutoff Current	V _{CB} = 30 V		100	nA
СВО		$V_{CB} = 30 \text{ V}$ $V_{CB} = 30 \text{ V}$, $T_{A}=100^{\circ}\text{C}$		10	uA
ІЕВО	Emitter Cutoff Current	V _{EB} = 4V		100	nA
		9_			
	RACTERISTICS* DC Current Gain	3, 37	70		
hfE	DC Current Gain	Ic = 100 mA, V _{CE} = 2 V	100	300	_
		I _C = 500 mA, V _{CE} = 2 V NZT660 NZT660A	250	550	
		Ic = 1 A, VcE = 2 V	80	330	
		$I_C = 3 \text{ A}, \text{ V}_{CE} = 2 \text{ V}$	25		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		300	mV
02(001)		I _C = 3 A, I _B = 300 mA NZT660		550	
		NZT660A		500	
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		1.25	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 1 A, V _{CE} = 2 V		1	V
SMALL S	IGNAL CHARACTERISTICS				
C _{obo}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1MHz		45	pF
f _T	Transition Frequency	I _C = 100 mA,V _{CE} = 5 V, f=100MHz	75		-
Dulca Tact	Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%				
i dise rest. i	r dise Width 3 300 μs, Duty Gydle 3 2.070				

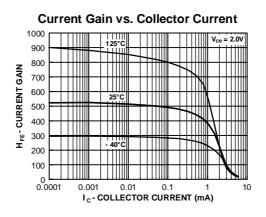
Typical Characteristics

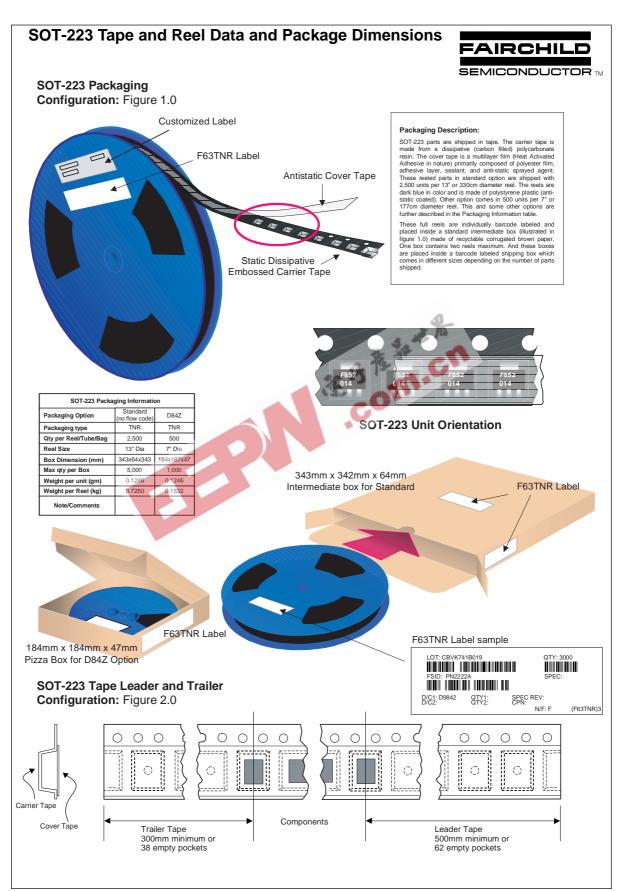


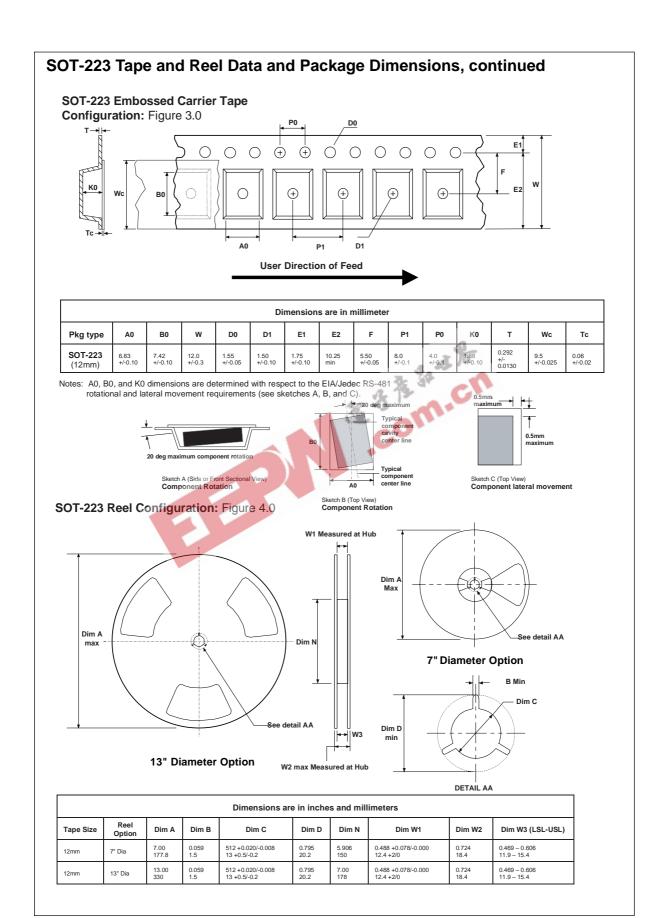












SOT-223 Tape and Reel Data and Package Dimensions, continued SOT-223 (FS PKG Code 47) Scale 1:1 on letter size paper Part Weight per unit (gram): 0.1246 0.256±0.008 [6.50±0.20] 0.122 3.10 0.114 2.90 0.129MAX. [3.28]ф0.004[0.1]MDASBS _0.1400+0.0060 3.56+0.15 0.059MAX. [1.50] $0.274^{+0.013}_{-0.010}$ EB-0.248 [6.30] -0.059MAX. 0.0900TYP. [2.29] 0.039 [0.99]TYP. -0.090 [2.29] LAND PATTERN RECOMMENDATION R0.0060±0.0020 [R0.15±0.05]TYP -GAGE PLANE 0.071 | 1.80 -0.061 | 1.55 -0.0630 [1.60] 0.0130 | 0.33 0.0090 | 0.23 0.010[0.25] 0.032 [0.82]MIN 10.0 TYP. 0.004 0.10 TYP_ R0.006±0.002 [R0.15±0.05]TYP. 0.067 [1.70] -SEATING PLANE NOTES: UNLESS OTHERWISE SPECIFIED 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES/ 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER. 2. REFERENCE JEDEC REGISTRATION TO-261, VARIATION AA, ISSUE A, DATED JAN 1990 SOT223, 4 LEADS

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